

HD74LVC1G66

Single Analog Switch

REJ03D0026-0300Z

Rev.3.00

Jul. 01, 2004

Description

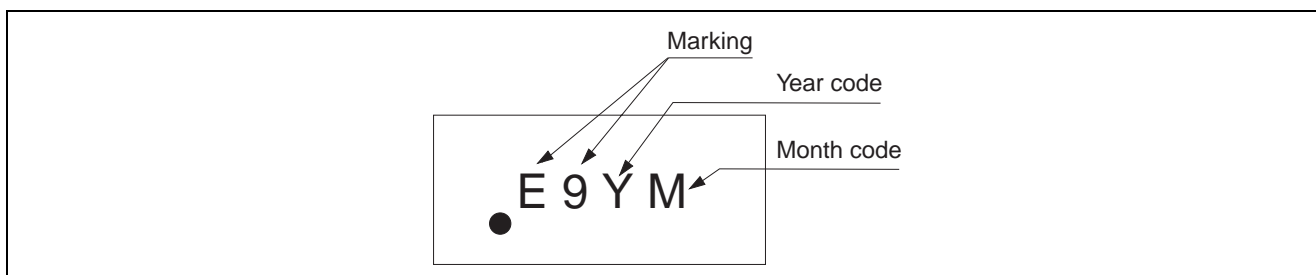
The HD74LVC1G66 has an analog switch in a 5-pin package. Switch section has its enable input control (CONT). High-level voltage applied to CONT turns on the switch section. Applications include signal gating chopping, modulation or demodulation (modem), and signal multiplexing for analog to digital to analog conversion systems. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as renesas uni logic series.
- Supply voltage range: 1.65 to 5.5 V
Operating temperature range: -40 to +85°C
- Control input: V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LVC1G66CPE	WCSP-5 pin	TBS-5V	CP	E (3,000 pcs/reel)
HD74LVC1G66CLE		TBS-5AV	CL	

Article Indication



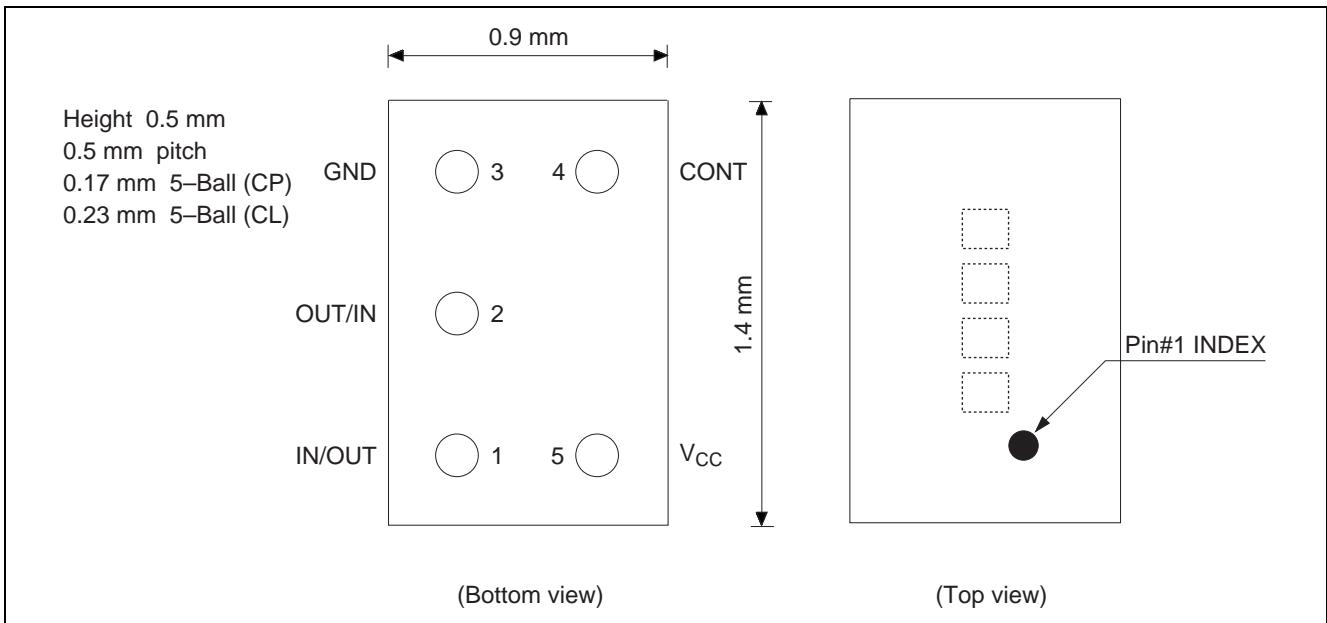
Function Table

Control	Switch
L	OFF
H	ON

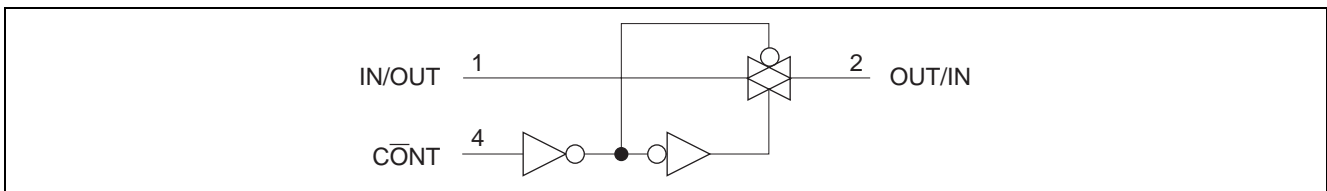
H: High level

L: Low level

Pin Arrangement



Logic Diagram



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V_{CC}	-0.5 to 6.5	V	
Input voltage range ^{*1}	V_I	-0.5 to 6.5	V	
Output voltage range ^{*1, 2}	V_O	-0.5 to $V_{CC} + 0.5$	V	Output : H or L
Control Input clamp current	I_{IK}	-50	mA	$V_I < 0$
Output clamp current	I_{OK}	± 50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	± 50	mA	$V_O = 0$ to V_{CC}
Continuous current through V_{CC} or GND	I_{CC} or I_{GND}	± 100	mA	
Package Thermal impedance	θ_{ja}	154	°C/W	CP
		132		CL
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

- The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- This value is limited to 5.5 V maximum.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V_{CC}	1.65	5.5	V	
Control Input voltage range	V_I	0	5.5	V	
Input/Output voltage range	$V_{I/O}$	0	V_{CC}	V	
Input transition rise or fall rate	$\Delta t / \Delta v$	0	20	ns / V	$V_{CC} = 1.65$ to 1.95 V, 2.3 to 2.7 V
		0	10		$V_{CC} = 3.0$ to 3.6 V
		0	10		$V_{CC} = 4.5$ to 5.5 V
Operating free-air temperature	T_a	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristics

$T_a = -40$ to 85°C

Item	Symbol	V_{CC} (V)	Min	Typ	Max	Unit	Test condition
Input voltage	V_{IH}	1.65 to 1.95	$V_{CC} \times 0.65$	—	—	V	
		2.3 to 2.7	$V_{CC} \times 0.7$	—	—		
		3.0 to 3.6	$V_{CC} \times 0.7$	—	—		
		4.5 to 5.5	$V_{CC} \times 0.7$	—	—		
	V_{IL}	1.65 to 1.95	—	—	$V_{CC} \times 0.35$		
		2.3 to 2.7	—	—	$V_{CC} \times 0.3$		
		3.0 to 3.6	—	—	$V_{CC} \times 0.3$		
		4.5 to 5.5	—	—	$V_{CC} \times 0.3$		
On-state switch resistance	R_{ON}	1.65	—	13	30	Ω	$I_S = 4$ mA $V_I = V_{CC}$ or GND
		2.3	—	9	20		
		3.0	—	7.5	15		
		4.5	—	5.5	10		
Peak on resistance	$R_{ON(P)}$	1.65	—	74.5	120	Ω	$I_S = 4$ mA $V_I = V_{CC}$ to GND
		2.3	—	20	30		
		3.0	—	11.5	20		
		4.5	—	7.5	15		
Off-state switch leakage current	$I_{S(OFF)}$	5.5	—	—	± 1.0	μA	$V_I = V_{CC}$ and $V_O = \text{GND}$ or $V_I = \text{GND}$ and $V_O = V_{CC}$, $V_C = V_{IL}$
			—	—	$\pm 0.1^{*1}$		
On-state switch leakage current	$I_{S(ON)}$	5.5	—	—	± 1.0	μA	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$ $V_O = \text{Open}$
			—	—	$\pm 0.1^{*1}$		
Control input current	I_{IN}	5.5	—	—	± 1.0	μA	$V_{IN} = V_{CC}$ or GND
			—	—	$\pm 0.1^{*1}$		
Quiescent supply current	I_{CC}	5.5	—	—	10	μA	$V_{IN} = V_{CC}$ or GND
			—	—	1.0^{*1}		
	ΔI_{CC}	5.5	—	—	500	μA	$V_C = V_{CC} - 0.6$ V
Control input capacitance	C_{IC}	5.0	—	3.0	—	pF	
Switch terminal capacitance	$C_{I/O(OFF)}$	5.0	—	6.0	—	pF	
	$C_{I/O(ON)}$	5.0	—	13	—		

Note: 1. $T_a = 25^\circ\text{C}$

Switching Characteristics

$V_{CC} = 1.8 \pm 0.15 \text{ V}$

Item	Symbol	Ta = -40 to 85°C		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Max				
Propagation delay time*1	t _{PLH} t _{PHL}	—	2.0	ns	C _L = 30 pF, R _L = 1.0 kΩ	INOUT or OUTIN	OUTIN or INOUT
Enable time	t _{ZH} t _{ZL}	2.5	12.0				
Disable time	t _{HZ} t _{LZ}	2.2	10.0				

$V_{CC} = 2.5 \pm 0.2 \text{ V}$

Item	Symbol	Ta = -40 to 85°C		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Max				
Propagation delay time*1	t _{PLH} t _{PHL}	—	1.2	ns	C _L = 30 pF, R _L = 500 Ω	INOUT or OUTIN	OUTIN or INOUT
Enable time	t _{ZH} t _{ZL}	1.9	6.5				
Disable time	t _{HZ} t _{LZ}	1.4	6.9				

$V_{CC} = 3.3 \pm 0.3 \text{ V}$

Item	Symbol	Ta = -40 to 85°C		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Max				
Propagation delay time*1	t _{PLH} t _{PHL}	—	0.8	ns	C _L = 50 pF, R _L = 500 Ω	INOUT or OUTIN	OUTIN or INOUT
Enable time	t _{ZH} t _{ZL}	1.8	5.0				
Disable time	t _{HZ} t _{LZ}	2.0	6.5				

$V_{CC} = 5.0 \pm 0.5 \text{ V}$

Item	Symbol	Ta = -40 to 85°C		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Max				
Propagation delay time*1	t _{PLH} t _{PHL}	—	0.6	ns	C _L = 50 pF, R _L = 500 Ω	INOUT or OUTIN	OUTIN or INOUT
Enable time	t _{ZH} t _{ZL}	1.5	4.2				
Disable time	t _{HZ} t _{LZ}	1.4	5.0				

Note: 1. The propagation delay is calculated RC time constant of typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

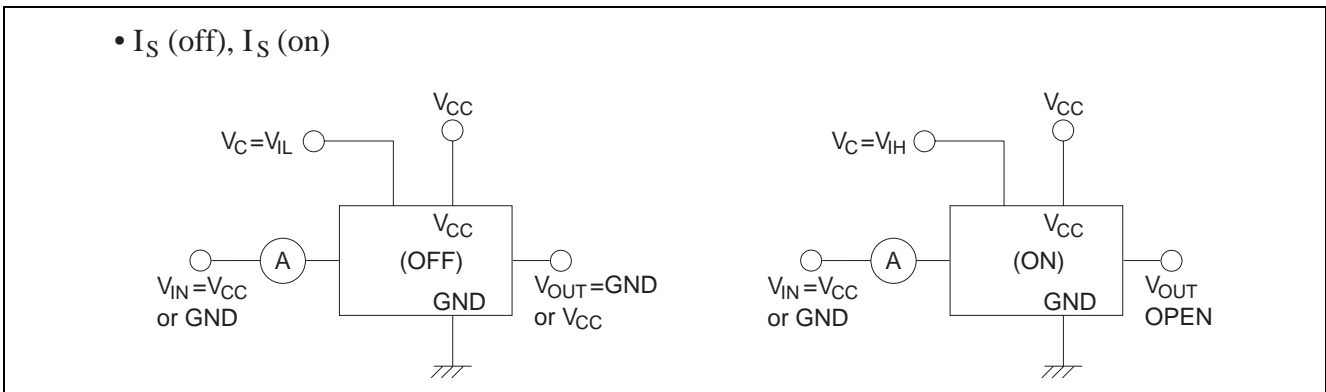
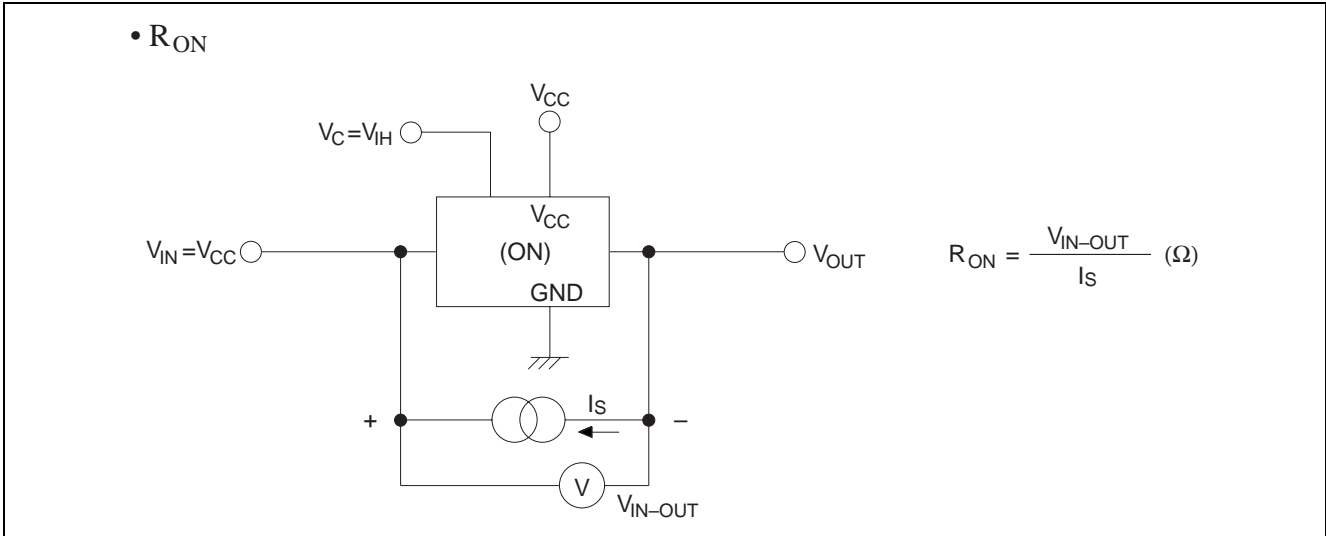
Analog Switch Characteristics

Item	V _{CC} (V)	Ta = 25°C			Unit	Test conditions	FROM (Input)	TO (Output)
		Min	Typ	Max				
Frequency response (Switch ON)	1.65	—	35	—	MHz	C _L = 50 pF, R _L = 600 Ω Adjust fin voltage to obtain 0dBm at output when fin is 1MHz (sine wave). Increase fin frequency until the dB-meter reads -3 dBm. 20 log(V _O /V _I) = -3 dBm	INOUT or OUTIN	OUTIN or INOUT
	2.3	—	120	—				
	3.0	—	175	—				
	4.5	—	195	—				
	1.65	—	>300	—	MHz	C _L = 5 pF, R _L = 50 Ω	INOUT or OUTIN	OUTIN or INOUT
	2.3	—	>300	—				
	3.0	—	>300	—				
	4.5	—	>300	—				
Crosstalk (Control input to signal output)	1.65	—	35	—	mV	C _L = 50 pF, R _L = 600 Ω Adjust RL value to obtain 0A at I _{IN/OUT} when fin is 1MHz (square wave)	CONT	OUTIN or INOUT
	2.3	—	50	—				
	3.0	—	70	—				
	4.5	—	100	—				
Feed through attenuation (Switch OFF)	1.65	—	-58	—	dB	C _L = 50 pF, R _L = 600 Ω Adjust fin voltage to obtain 0dBm at input when fin is 1MHz (sine-wave)	INOUT or OUTIN	OUTIN or INOUT
	2.3	—	-58	—				
	3.0	—	-58	—				
	4.5	—	-58	—				
	1.65	—	-42	—	dB	C _L = 5 pF, R _L = 50 Ω	INOUT or OUTIN	OUTIN or INOUT
	2.3	—	-42	—				
	3.0	—	-42	—				
	4.5	—	-42	—				
Sine-wave distortion	1.65	—	0.1	—	%	C _L = 50 pF, R _L = 10 kΩ fin = 1 kHz (sine-wave)	INOUT or OUTIN	OUTIN or INOUT
	2.3	—	0.025	—				
	3.0	—	0.015	—				
	4.5	—	0.01	—				
	1.65	—	0.15	—	%	C _L = 50 pF, R _L = 10 kΩ fin = 10 kHz (sine-wave)	INOUT or OUTIN	OUTIN or INOUT
	2.3	—	0.025	—				
	3.0	—	0.015	—				
	4.5	—	0.01	—				

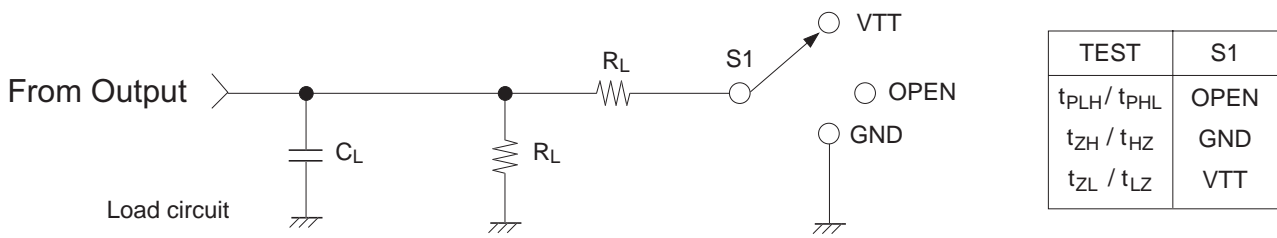
Operating Characteristics

Item	Symbol	V _{CC} (V)	Ta = 25°C			Unit	Test Conditions
			Min	Typ	Max		
Power dissipation capacitance	C _{PD}	1.8	—	8	—	pF	f = 10 MHz
		2.5	—	9	—		
		3.3	—	9	—		
		5.0	—	11	—		

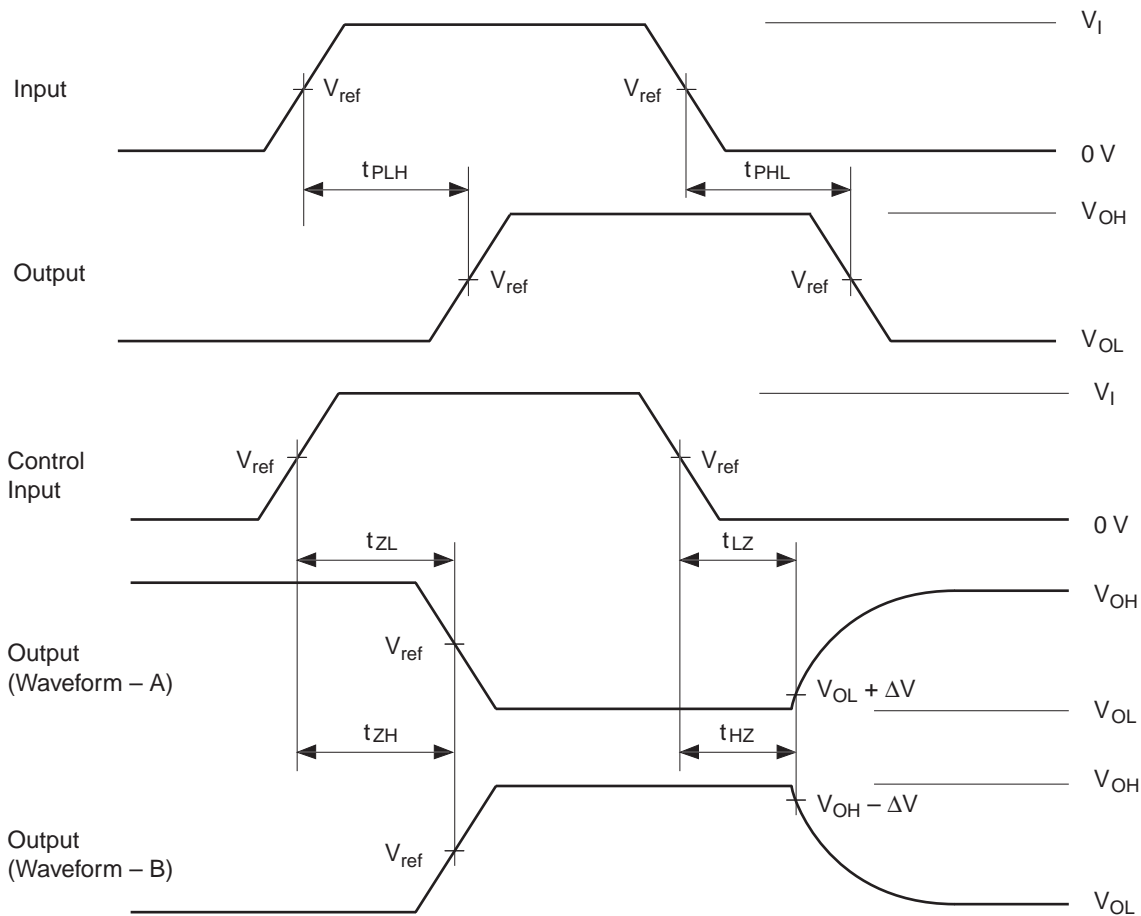
Test Circuit



Test Circuit (cont.)

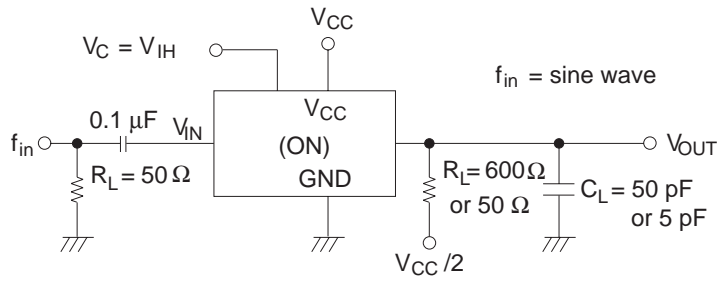


V_{CC} (V)	INPUTS		V_{ref}	VTT	C_L	R_L	ΔV
	V_I	t_r / t_f					
1.8 ± 0.15	V_{CC}	≤ 2 ns	$V_{CC} / 2$	$2 \times V_{CC}$	30 pF	1.0 k Ω	0.15 V
2.5 ± 0.2	V_{CC}	≤ 2 ns	$V_{CC} / 2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
3.3 ± 0.3	V_{CC}	≤ 2.5 ns	$V_{CC} / 2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V
5.0 ± 0.5	V_{CC}	≤ 2.5 ns	$V_{CC} / 2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V

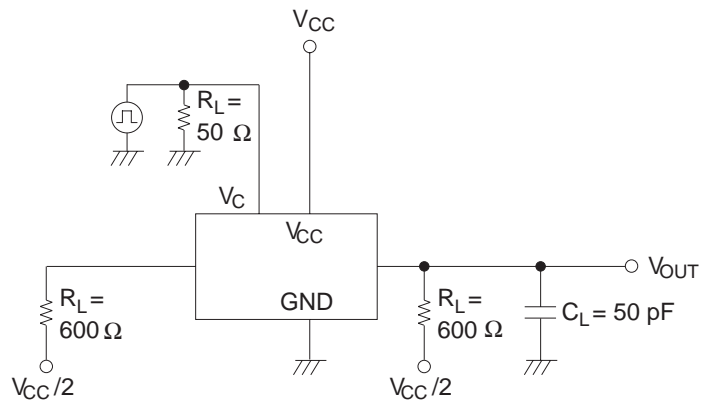


- Notes:
1. C_L includes probe and jig capacitance.
 2. Waveform-A is for an output with internal conditions such that the output is low except when disabled by the output control.
 3. Waveform-B is for an output with internal conditions such that the output is high except when disabled by the output control.
 4. All input pulses are supplied by generators having the following characteristics:
 $PRR \leq 10$ MHz, $Z_o = 50 \Omega$.
 5. The output are measured one at a time with one transition per measurement.

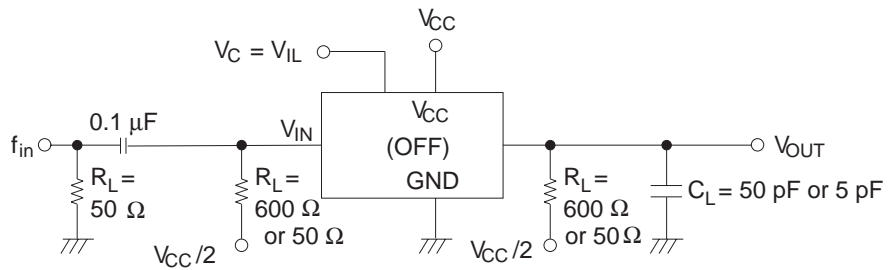
Frequency response (Switch ON)



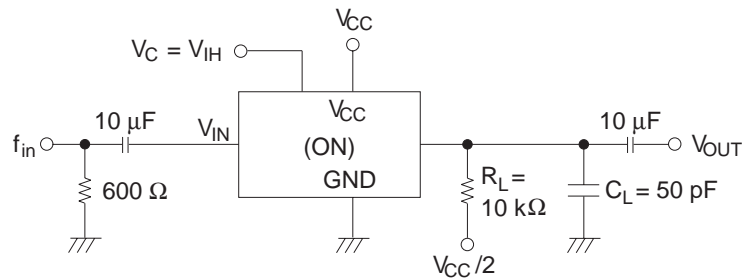
Crosstalk (Control input to signal output)



Feedthrough attenuation (Switch OFF)



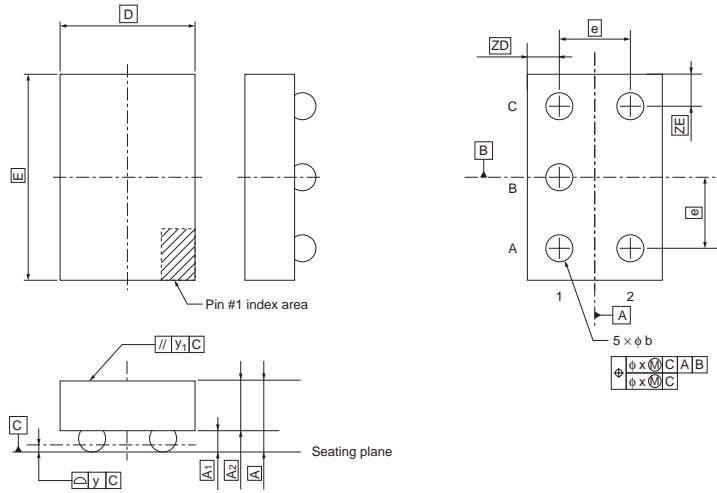
Sine-wave distortion



Package Dimensions

TBS-5V

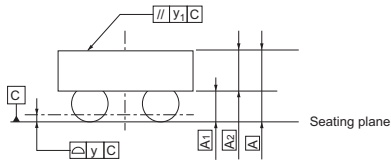
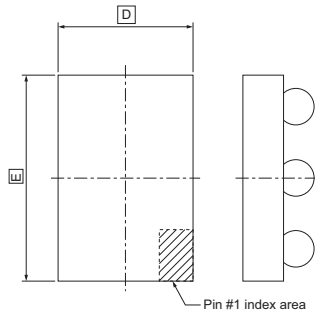
EIAJ Package Code	JEDEC Code	Mass (g)	Lead Material
—	—	0.001	—



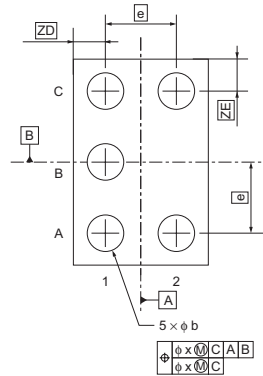
Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	0.50
A ₁	0.10	—	0.15
A ₂	—	—	0.35
b	0.15	0.17	0.19
D	—	0.90	—
E	—	1.40	—
e	—	0.50	—
x	—	—	0.05
y	—	—	0.05
y ₁	—	—	0.20
ZD	—	0.20	—
ZE	—	0.20	—

TBS-5AV

EIAJ Package Code	JEDEC Code	Mass (g)	Lead Material
—	—	0.001	



*Reference value.



Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	—	—	0.50
A ₁	0.155	—	0.185
A ₂	—	—	(0.315)*
b	0.20	—	0.25
D	—	0.90	—
E	—	1.40	—
e	—	0.50	—
x	—	—	0.05
y	—	—	0.05
y ₁	—	—	0.20
ZD	—	0.20	—
ZE	—	0.20	—

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